



# 《风光欣》技术资料

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## 2SB772

PNP EPITAXIAL SILICON TRANSISTOR

AUDIO FREQUENCY POWER AMPLIFIER

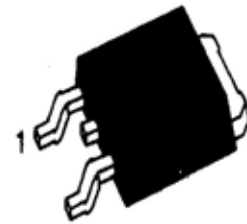
LOW SPEED SWITCHING

\*Complement to 2SD882

### ABSOLUTE MAXIMUM RATINGS(TA=25 )

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V <sub>CB0</sub>	-40	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-30	V
Emitter -Base Voltage	V <sub>EB0</sub>	-5	V
Collector Current (DC)	I <sub>c</sub>	-3	A
Collector Current (Pulse)	I <sub>c</sub>	-7	A
Base Current (DC)	I <sub>B</sub>	-0.6	A
Collector Dissipation (T <sub>c</sub> =25 )	P <sub>c</sub>	10	W
Collector Dissipation (T <sub>a</sub> =25 )	P <sub>c</sub>	1	W
Junction Temperature	T <sub>J</sub>	150	
Storage Temperature	T <sub>STG</sub>	-55 ~150	

SOT-252



1. Base 2. Collector 3. Emitter

### ELECTRICAL CHARACTERISTICS(TA=25 )

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Cut-off Current	I <sub>CB0</sub>	V <sub>CB</sub> = -30V, I <sub>E</sub> =0			-1	μ A
Emitter-Cut-off Current	I <sub>EB0</sub>	V <sub>EB</sub> = -3V, I <sub>c</sub> =0			-1	μ A
*DC Current Gain	h <sub>FE1</sub>	V <sub>CE</sub> = -2V, I <sub>c</sub> = -20mA	30	150		
	h <sub>FE2</sub>	V <sub>CE</sub> = -2V, I <sub>c</sub> = -1A	60	160	400	
*Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>c</sub> = -2A, I <sub>B</sub> = -0.2A		-0.3	-0.5	V
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	I <sub>c</sub> = -2A, I <sub>B</sub> = -0.2A		-1.0	-2.0	V
Current Gain-Bandwidth Product	f <sub>T</sub>	V <sub>CE</sub> = -5V, I <sub>E</sub> = -0.1A		90		MHZ
Output Capacitance	C <sub>OB</sub>	V <sub>CB</sub> = -10V, I <sub>E</sub> =0, f=1MHZ		45		pF

\*Pulse Test :PW<350US, Duty Cycle<2%

### hFE (2) CLASSIFICATION

Classification	R	Q	P	I
HFE(2)	60-120	160-200	160-320	200-400